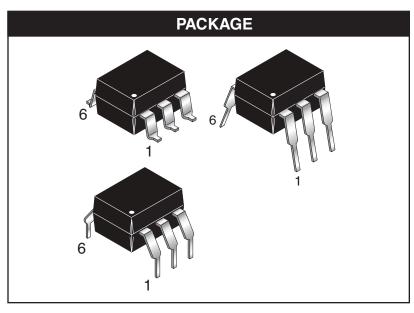
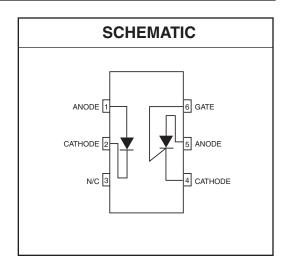
H11C1 H11C2 H11C3 H11C4 H11C5 H11C6





DESCRIPTION

The H11C series consists of a gallium-arsenide infrared emitting diode optically coupled with a light activated silicon controlled rectifier in a dual-in-line package

FEATURES

- · High efficiency, low degradation, liquid epitaxial LED
- Underwriters Laboratory (UL) recognized fl File #E90700
- VDE recognized (File #94766) ordering option .300. (e.g., H11C1.300)
- 200V/400V Peak blocking voltage
- High isolation voltage 5300V AC (RMS)

APPLICATIONS

- · Low power logic circuits
- Telecommunications equipment
- · Portable electronics
- Solid state relays
- Interfacing coupling systems of different potentials and impedances.
- 10 A, T²L compatible, solid state relay
- 25 W logic indicator lamp driver
- 200 V symmetrical transistor coupler (H11C1, H11C2, H11C3)
- 400 V symmetrical transistor coupler (H11C4, H11C5, H11C6)



H11C1 H11C2 H11C3 H11C4 H11C5 H11C6

Parameter	Symbol	Device	Value	Units
TOTAL DEVICE				
Storage Temperature	T _{STG}	All	-55 to +150	°C
Operating Temperature	T _{OPR}	All	-55 to +100	°C
Lead Solder Temperature	T _{SOL}	All	260 for 10 sec	°C
EMITTER				
Continuous Forward Current	I _F	All	60	mA
Reverse Voltage	V _R	All	6	V
Forward Current - Peak (1 µs pulse, 300 pps)	I _{F(pk)}	All	3.0	Α
LED Power Dissipation	D	All	100	mW
Derate above 25°C	P _D All		1.33	mW/°C
DETECTOR				
Power Dissipation (ambient)	5 411		400	mW
Derate linearly above 25°C ambient	P_{D}	All	5.3	mW/°C
Power Dissipation (case)	Б	All	1	W
Derate linearly above 25°C case	P_{D}	All	13.3	mW/°C
Peak Reverse Gate Voltage	V _{GR}	All	6	V
RMS On-State Current	I _{DM (RMS)}	All	300	mA
Peak On-State Current (100 μS, 1% duty cycle)	I _{DM (Peak)}	All	10	А
Surge Current (10ms)	I _{DM (Surge)}	All	5	Α
Peak Forward Voltage	V_{DM}	H11C1, H11C2, H11C3	200	V
Peak Forward Voltage	V_{DM}	H11C4, H11C5, H11C6	400	V



H11C1 H11C2 H11C3 H11C4 H11C5 H11C6

ELECTRICAL CHARACTERISTICS ($T_A = 25^{\circ}C$ Unless otherwise specified.)

INDIVIDUAL COMPONENT CHARACTERISTICS								
Parameter	Test Conditions	Symbol	Device	Min	Тур*	Max	Unit	
EMITTER								
Input Forward Voltage	I _F = 10 mA	V _F	All		1.2	1.5	V	
Reverse Leakage Current	V _R = 3 V	I _R	All			10	μA	
Capacitance	V _F = 0 V, f = 1.0 MHz	CJ	All		50		pF	
DETECTOR								
Off-State Voltage	$R_{GK} = 10k\Omega, T_A = 100^{\circ}C, I_D = 50\mu A$	/	H11C1, H11C2, H11C3	200			J v	
On-State voltage	$R_{GK} = 10k\Omega, T_A = 100^{\circ}C, I_D = 150\mu A$	V_{DM}	H11C4, H11C5, H11C6	400			'	
Reverse Voltage	$R_{GK} = 10k\Omega, T_A = 100^{\circ}C, I_R = 50\mu A$	\/	H11C1, H11C2, H11C3	200			V	
neverse voltage	rge $R_{GK} = 10kΩ, T_A = 100°C, I_B = 150μA$		H11C4, H11C5, H11C6	400			'	
On-State Voltage	I _{TM} = 300 mA	V _{TM}	All		1.2	1.3	٧	
Off-State Current	$V_{DM} = 200V, T_A = 100^{\circ}C, I_F = 0 \text{ mA},$ $R_{GK} = 10k\Omega$		H11C1, H11C2, H11C3			50	μΑ	
On-State Current	$V_{DM} = 400V, T_A = 100^{\circ}C, I_F = 0 \text{ mA},$ $R_{GK} = 10k\Omega$	I _{DM}	H11C4, H11C5, H11C6			150		
Reverse Current	$V_{RM} = 200 \text{ V}, T_A = 100 \text{ °C}, I_F = 0 \text{ mA},$ $R_{GK} = 10 \text{k}\Omega$		H11C1, H11C2, H11C3			50	μА	
Theverse Currelli	variety $V_{RM} = 400 \text{ V}, T_A = 100 \text{ °C}, I_F = 0 \text{ mA}, R_{GK} = 10 \text{k}\Omega$		H11C4, H11C5, H11C6			150	μA	

TRANSFER CHARACTERISTICS (T _A = 25°C Unless otherwise specified.)							
Characteristics	Test Conditions	Symbol	Device	Min	Тур*	Max	Units
	$V_{AK} = 50 \text{ V}, R_{GK} = 10 \text{ k}\Omega$		H11C1,H11C2, H11C4, H11C5			20	
Input Current to Trigger	7	١.	H11C3, H11C6		30	mA	
	$V_{AK} = 100 \text{ V}, R_{GK} = 27 \text{ k}\Omega$	ГFT	H11C1,H11C2, H11C4, H11C5			11	
			H11C3, H11C6			14	
Coupled dv/dt, input to output (figure 8)		dv/dt	ALL	500			V/µS

^{*}Typical values at $T_A = 25^{\circ}C$



H11C1 H11C2 H11C3 H11C4 H11C5 H11C6

ISOLATION CHARACTERISTICS						
Characteristic	Test Conditions	Symbol	Min	Тур*	Max	Units
Isolation Voltage	(t = 1 min.) (note 1)	V _{ISO}	5300			V
Isolation Resistance	(note 1) (V _{I-O} = 500 VDC)	R _{ISO}	10 ¹¹			Ω
Isolation Capacitance	(note 1) (f = 1 MHz, V _{I-O} = 0)	C _{I-O}		0.8		pF

^{*}Typical values at $T_A = 25^{\circ}C$

Note

1. For this test, LED pins 1 and 2 are common, and SCR pins 4, 5 and 6 are common.

H11C1 H11C2 H11C3 H11C4 H11C5 H11C6

Figure 1. LED Forward Current vs. Forward Voltage

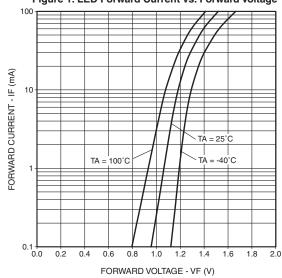


Figure 2. Trigger Current vs Anode-Cathode Voltage 100 IFT, NORMALIZED TRIGGER CURRENT $R_{GK} = 300 \text{ ohn}$ R_{GK} = 1K $R_{GK} = 10K$ $\begin{array}{l} \text{NORMALIZED TO} \\ \text{V}_{\text{AK}} = 50 \text{V} \end{array}$ R_{GK} = 10K T_A = 25°C 10 100 V_{AK} , ANODE-CATHODE VOLTAGE (V)

Figure 3. Input Trigger Current vs. Temperature

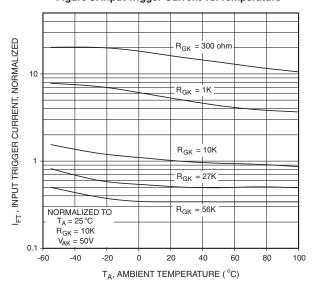
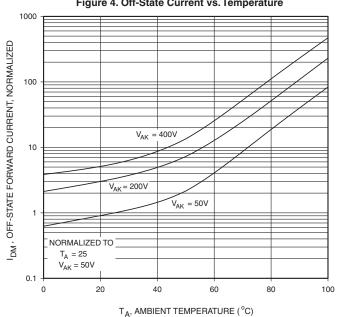


Figure 4. Off-State Current vs. Temperature



H11C1 H11C2 H11C3 H11C4 H11C5 H11C6

Figure 5. Forward Blocking Voltage, \mathbf{V}_{DM} vs. Temperature 700 650 V_{DM}, FORWARD BLOCKING VOLTAGE (V) R_{GK} = 10K, 20K 600 550 $R_{GK} = 50K$ 500 R_{GK} = 100K 450 400 350 300 -100 T_A , AMBIENT TEMPERATURE ($^{\circ}$ C)

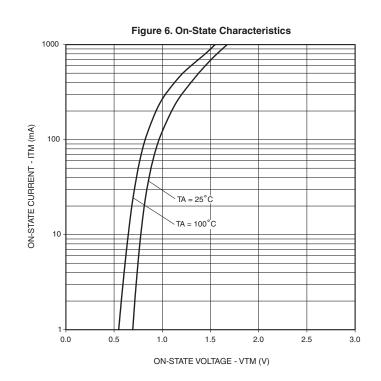


Figure 7. Holding Current, I_H vs. Temperature

10000

R_{GK} = 300 ohm

R_{GK} = 10K

R_{GK} = 10K

R_{GK} = 27K

R_{GK} = 56K

R_{GK} = 56K

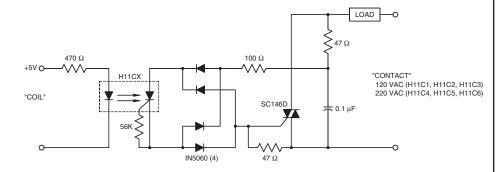
T_A. AMBIENT TEMPERATURE (⁰C)

H11C1 H11C2 H11C3 H11C4 H11C5 H11C6

TYPICAL APPLICATIONS

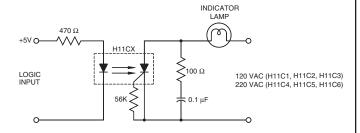
10A, T²L COMPATIBLE, SOLID STATE RELAY

Use of the H11C4 for high sensitivity, 5300 V isolation capability, provides this highly reliable solid state relay design. This design is compatible with 74, 74S and 74H series T²L logic systems inputs and 120V AC (H11C1, H11C2, H11C3) or 220V AC (H11C4, H11C5, H11C6) loads up to 10A.



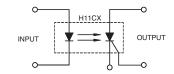
25W, LOGIC INDICATOR LAMP DRIVER

The high surge capability and non-reactive input characteristics of the H11C allow it to directly couple, without buffers, T^2L and DTL logic to indicator alarm devices, without danger of introducing noise and logic glitches.



200V/400V SYMMETRICAL TRANSISTOR COUPLER

Use of the high voltage PNP portion of the H11C provides a 400V transistor capable of conducting positive and negative signals with current transfer ratios of over 1%. This function is useful in remote instrumentation, high voltage power supplies and test equipment. Care should be taken not to exceed the H11C 400mW power dissipation rating when used at high voltages.



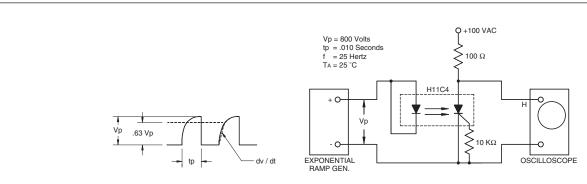
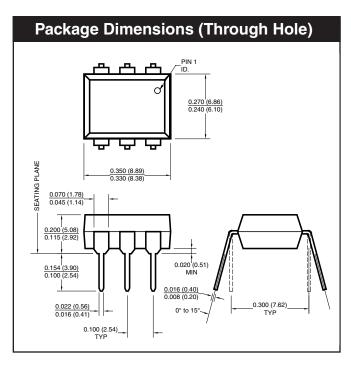
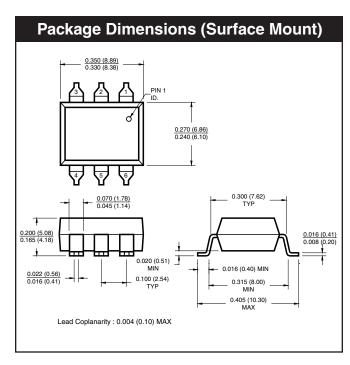


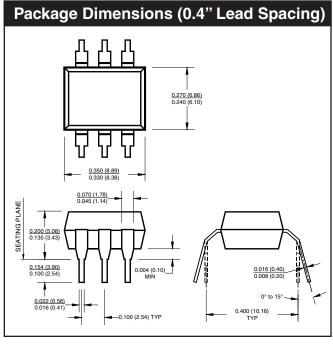
Fig. 8 Coupled dv/dt - Test Circuit

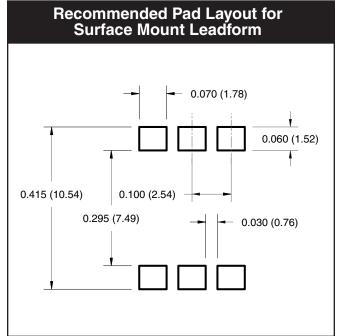


H11C1 H11C2 H11C3 H11C4 H11C5 H11C6









Note

All dimensions are in inches (millimeters)

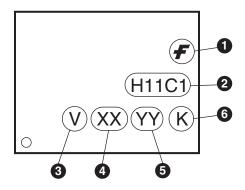


H11C1 H11C2 H11C3 H11C4 H11C5 H11C6	H11C1	H11C2	H11C3	H11C4	H11C5	H11C6
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ORDERING INFORMATION

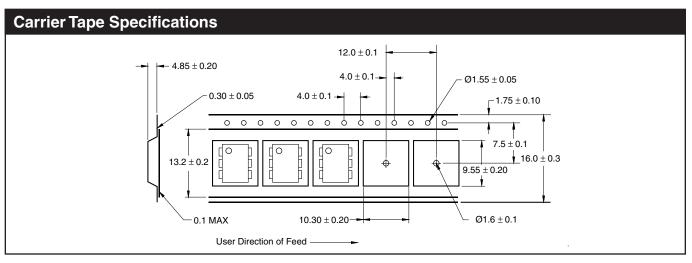
Option	Order Entry Identifier	Description
S	.S	Surface Mount Lead Bend
SD	.SD	Surface Mount; Tape and Reel
W	.W	0.4" Lead Spacing
300	.300	VDE 0884
300W	.300W	VDE 0884, 0.4" Lead Spacing
3S	.3\$	VDE 0884, Surface Mount
3SD	.3SD	VDE 0884, Surface Mount, Tape and Reel

MARKING INFORMATION

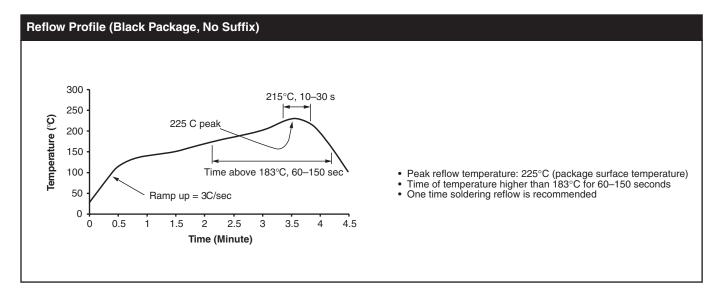


Definitions				
1	Fairchild logo			
2	Device number			
3	VDE mark (Note: Only appears on parts ordered with VDE option – See order entry table)			
4	Two digit year code, e.g., '03'			
5	Two digit work week ranging from '01' to '53'			
6	Assembly package code			

H11C1 H11C2 H11C3 H11C4 H11C5 H11C6



NOTEAll dimensions are in inches (millimeters)





H11C1 H11C2 H11C3 H11C4 H11C5 H11C6

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- A critical component in any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.